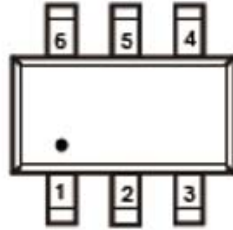
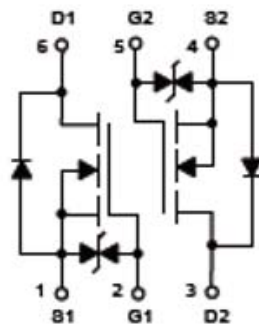




.....'B!7 \Ubby''9b \UbWY a Ybh' AcXY' :]Y`X'9ZZYWh'HfUbg]ghcf''



Dot denotes Pin1



SOT-363

DfcXiWh'Gi a aUfm'

$V_{DS}$	60V
$I_D$	300mA
$R_{DS(ON)}$ ( at $V_{GS}=10V$ )	2.5ohm
$R_{DS(ON)}$ ( at $V_{GS}=4.5V$ )	3.0ohm
ESD Protected Up to 2.0KV (HBM)	

; YbYfU''8YgWf]dh]cb'

- Trench Power MV MOSFET technology
- Voltage controlled small signal switch
- Low input Capacitance
- Fast Switching Speed
- Low Input / Output Leakage
- Part no. with suffix "Q" means AEC-Q101 qualified

5dd']WUh]cbg'

- Battery operated systems
- Solid-state relays
- Direct logic-level interface TTL/CMOS

5Vgc`ihY'AUI]a ia'FUh]b[g'(T<sub>A</sub>=25 unless otherwise noted)

DUfU a YhYf'		Gma Vc''	@]a ]h'	I b]h'
Drain-source Voltage		$V_{DS}$	60	V
Gate-source Voltage		$V_{GS}$	±20	V
Drain Current	T <sub>A</sub> =25°C @ Steady State	$I_D$	300	mA
	T <sub>A</sub> =70°C @ Steady State		240	
Pulsed Drain Current <sup>A</sup>		$I_{DM}$	1.5	A
Total Power Dissipation @ T <sub>A</sub> =25°C		$P_D$	300	mW
Thermal Resistance Junction-to-Ambient @ Steady State <sup>B</sup>		$R_{JA}$	416	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 +150	°C

CfXYf]b[-bZcf a Uh]cb'(Example)

DF9:9F98'D#B'	D57?-B; 7C89'	Auf_]b['	A=B-A I A' D57?5; 9fidWgt.	-BB9F'6CL' E I 5BH=HMfidWgt.	C I H9F'75FHCB' E I 5BH=HMfidWgt.	89@=J9FM'AC89
2N7002KCDWQ	F2	72KC	3000	30000	120000	7" reel



# &B+\$\$&?78KE'

9`YWhf]WU`7 \UfUWhYf]gh]Wg` (T<sub>J</sub>=25 unless otherwise noted)

DUFU a YhYf'	Gm a Vc''	7 cbX]h]cbg'	A]b'	Hmd'	AUI'	I b]hg'
<b>GhUh]W' DUFU a YhYf'</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	60			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ± 20V, V <sub>DS</sub> =0V			± 10	μA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA	1	1.5	2.5	V
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> =300mA		1.9	2.5	
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> =200mA		2.0	3.0	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =300mA, V <sub>GS</sub> =0V			1.2	V
Maximum Body-Diode Continuous Current	I <sub>S</sub>				300	mA
<b>8mbU a ]W' DUFU a YhYfg</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, f=1MHZ		27		pF
Output Capacitance	C <sub>oss</sub>			3		
Reverse Transfer Capacitance	C <sub>rss</sub>			2		
<b>Gk]hW\]b [ 'DUFU a YhYfg</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =30V, I <sub>D</sub> =0.3A		1.65	2.4	nC
Turn-on Delay Time	t <sub>D(on)</sub>	V <sub>GS</sub> =10V, V <sub>DD</sub> =30V, I <sub>D</sub> =300mA, R <sub>GEN</sub> =6		6.5		ns
Turn-off Delay Time	t <sub>D(off)</sub>			9.6		
Reverse recovery Time	t <sub>rr</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =300mA, V <sub>R</sub> =25V, di/dt=-100A/μs		24		ns

A. Pulse Test: Pulse Width 300us, Duty cycle 2%.

B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

.....



'Hmd]WU''DYfZcf a UbWY'7 \UfUWhYf]gh]Wg'

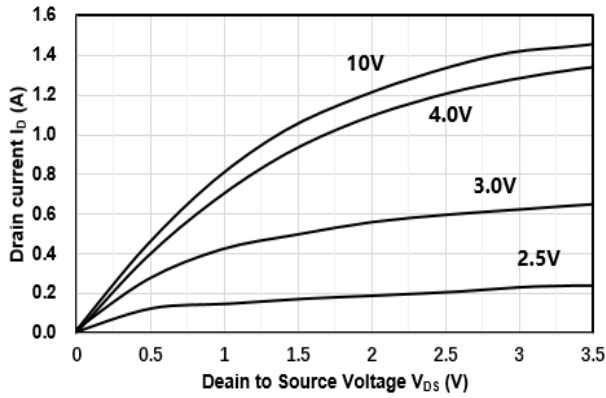


Figure1. Output Characteristics

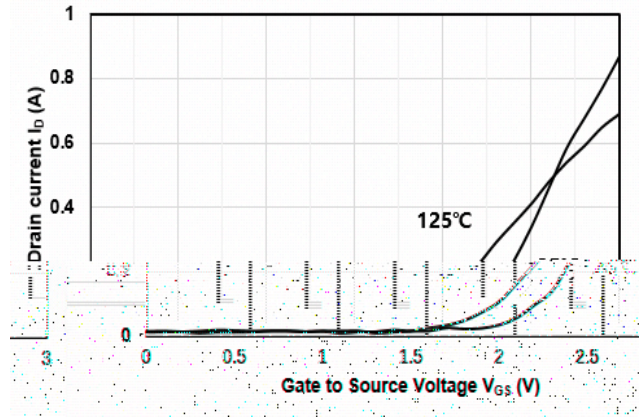


Figure2. Transfer Characteristics

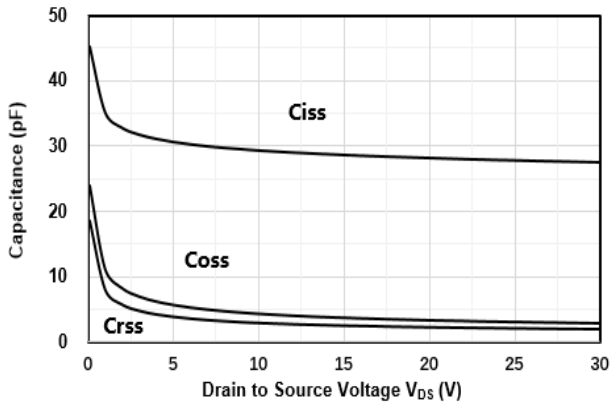


Figure3. Capacitance Characteristics

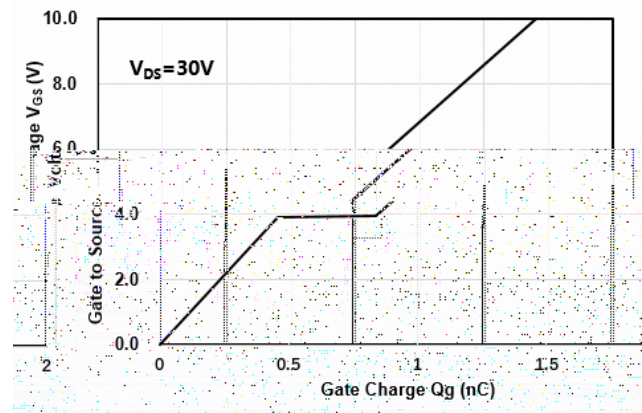


Figure4. Gate Charge

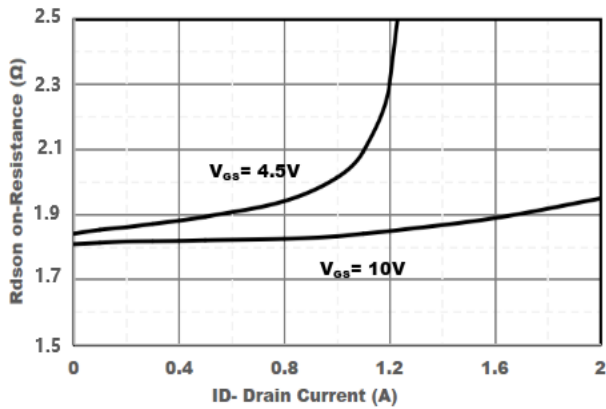


Figure5. Drain-Source on Resistance

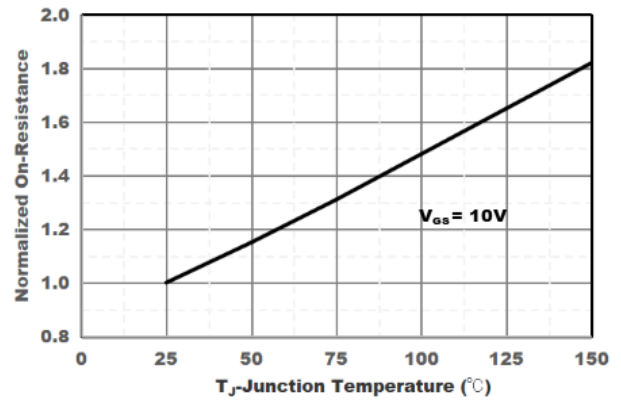


Figure6. Drain-Source on Resistance

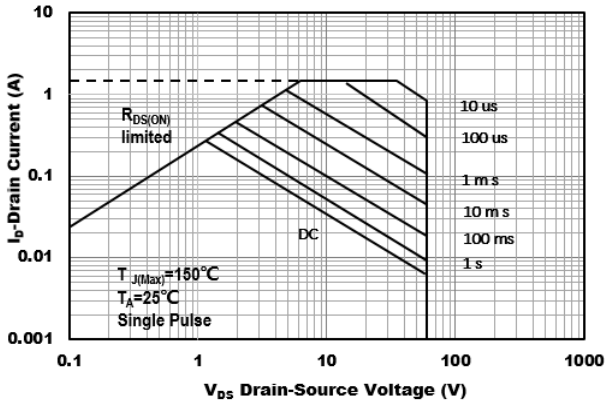


Figure7. Safe Operation Area

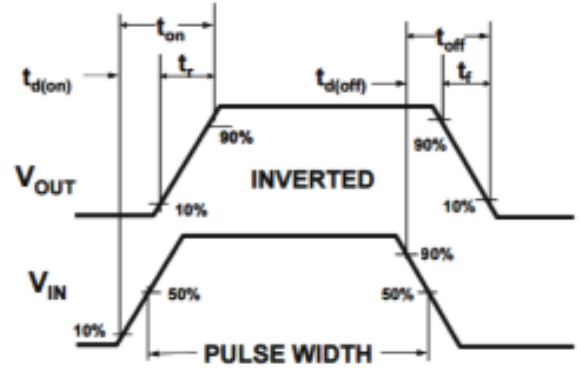
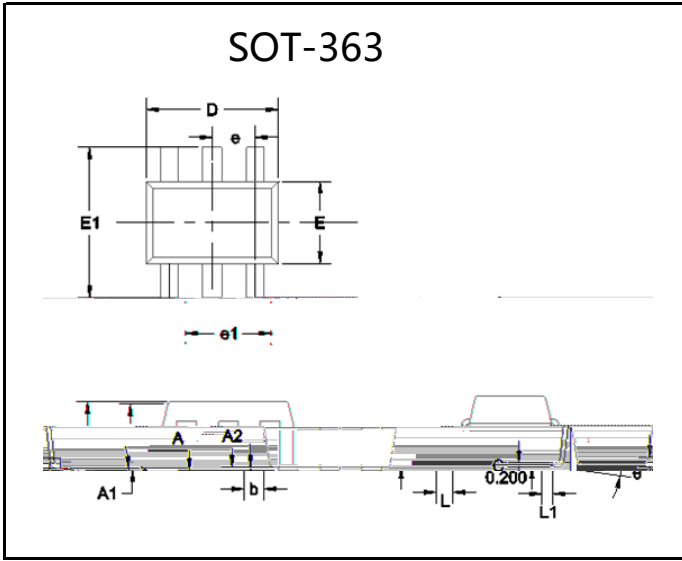


Figure8. Switching wave

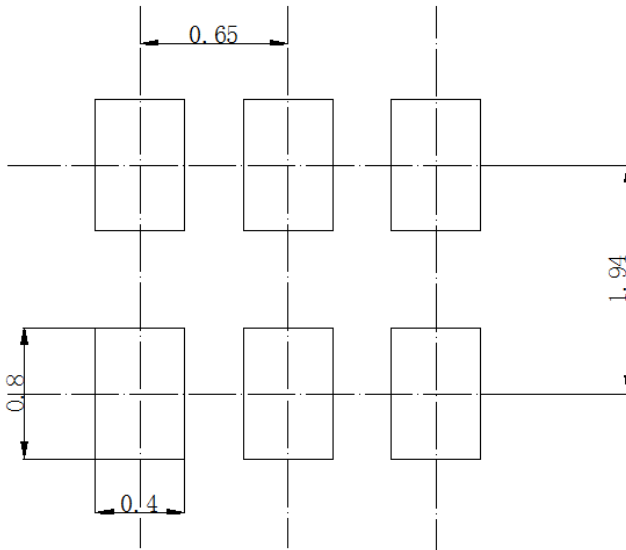


GCH!' \* ' 'DUW\_U[Y'C ih]bY'8]a Ybg]cbg'



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.035	0.043	0.90	1.10	
A1	0.000	0.004	0.00	0.10	
A2	0.035	0.039	0.90	1.00	
b	0.006	0.014	0.15	0.35	
c	0.002	0.010	0.05	0.25	
D	0.071	0.087	1.80	2.20	
E	0.045	0.053	1.15	1.35	
E1	0.085	0.096	2.15	2.45	
e	0.026Typ		0.65Typ		
e1	0.047	0.055	1.20	1.40	
L	0.021Typ		0.525Typ		
L1	0.010	0.018	0.26	0.46	
	0°	8°	0°	8°	

GCH!' \* ' 'Gc`XYf]b[ : cchdf]bh'



Unit mm'



8]gW'U]a Yf'

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F9J'	9 : : 97H-J9'85H9	F9J=G-CB'' <=GHCFM	DF9D5F98'
1.0	2021.06.11	New release	Zhenzhong Zhao